

ABSTRACT OF THE DISCLOSURE

ETCHING SOLUTION FOR SELECTIVELY REMOVING SILICON OVER SILICON-GERMANIUM ALLOY FROM A SILICON-GERMANIUM/ SILICON STACK DURING MANUFACTURE OF A SEMICONDUCTOR DEVICE

Etching compositions suitable for the selective removal of silicon over silicon-germanium from a microelectronic device comprising: water; at least one of a quaternary ammonium hydroxide compound and an amine compound; water-miscible solvent; optionally surfactant and optionally corrosion inhibitor; and the method of using the etching composition for the selective removal.

(No drawing to be published)